DATA SHEET

SILICON TRANSISTOR 2881578

PNP SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

The 2SB1578 features high current capacity in small dimension and is ideal for DC/DC converters and mortor drivers.

FEATURES

NEC

- New package with dimensions in between those of small signal and power signal package
- High current capacitance
- Low collector saturation voltage
- · Complementary transistor with 2SD2425

QUALITY GRADES

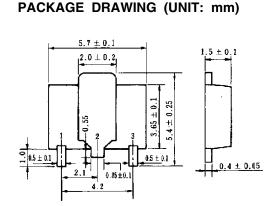
Standard

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.



	1			
Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-60	V
Collector to emitter voltage	VCEO		-60	V
Emitter to base voltage	VEBO		-6.0	V
Collector current (DC)	IC(DC)		-5.0	А
Collector current (pulse)	IC(pulse)	$PW \le 10 \text{ ms}$, duty cycle $\le 50 \%$	-7.0	А
Base current (DC)	IB(DC)		-1.0	А
Total power dissipation	P⊤	7.5 $\text{cm}^2 \times 0.7$ mm ceramic board used	2.0	W
Junction temperature	Tj		150	°C
Storage temperature	Tstg		-55 to +150	°C

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



Electrode connection

1: Emitter 2: Collector

3: Base

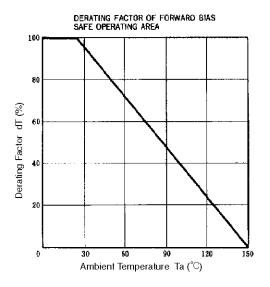
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

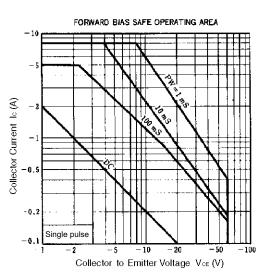
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$			-10	μA
Emitter cutoff current	Іево	$V_{EB} = -6.0 \text{ V}, \text{ Ic} = 0$			-10	μA
DC current gain	h _{FE1}	$V_{CE} = -1.0 \text{ V}, \text{ Ic} = -0.1 \text{ A}$	60	220		-
DC current gain	hfe2	Vce = -1.0 V, Ic = -2.0 A	100	200	400	_
DC current gain	hfeз	Vce = -2.0 V, Ic = -5.0 A	50	150		-
Collector saturation voltage	VCE(sat)	Ic = -2.0 A, Iв = -0.2 A		-180	-300	mV
Base saturation voltage	VBE(sat)	Ic = -2.0 A, Iв = -0.2 A		-0.9	-1.2	V
Turn-on time	ton	Ic = -2.0 A, Vcc = -10 V		0.6		μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.2 \text{ A}$ $R_L = 5.0 \Omega$		0.55		μs
Fall time	tr			0.05		μs

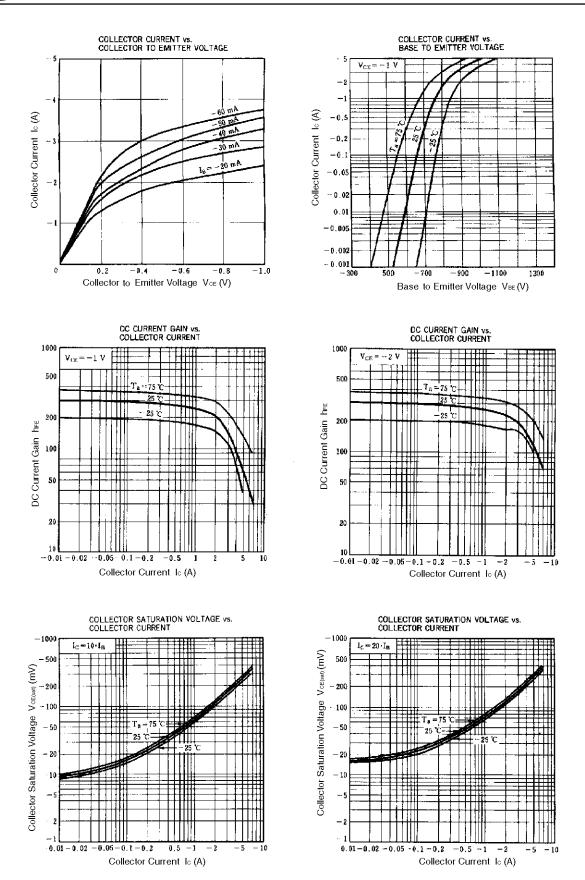
hfe CLASSIFICATION

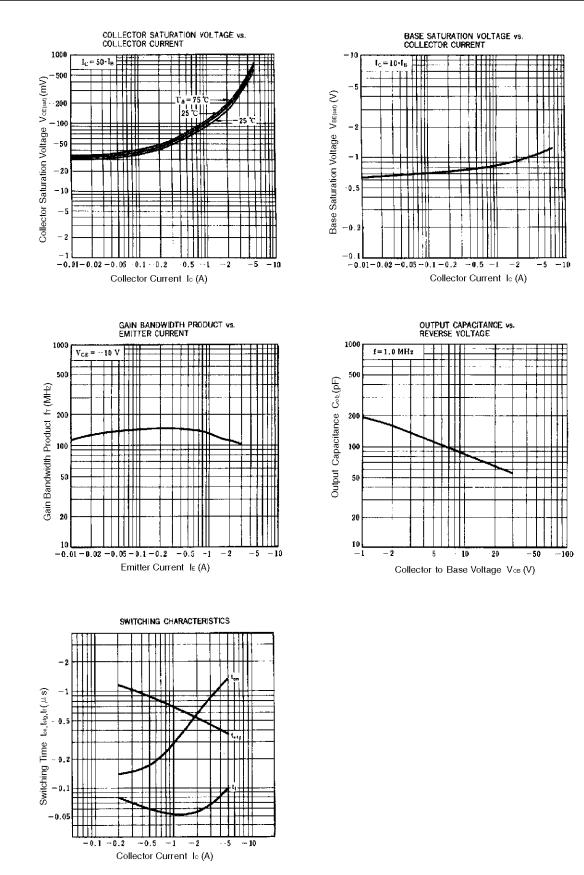
Marking	GB1	GB2	GB3	
hFE2	100 to 200	160 to 320	200 to 400	

TYPICAL CHARACTERISTICS (Ta = 25°C)









[MEMO]

- The information in this document is current as of July, 2001. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from the use of NEC semiconductor products listed in this document or any other liability arising from the use of such products. No license, express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative
 purposes in semiconductor product operation and application examples. The incorporation of these
 circuits, software and information in the design of customer's equipment shall be done under the full
 responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third
 parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers
 agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize
 risks of damage to property or injury (including death) to persons arising from defects in NEC
 semiconductor products, customers must incorporate sufficient safety measures in their design, such as
 redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:

"Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products developed based on a customer-designated "quality assurance program" for a specific application. The recommended applications of a semiconductor product depend on its quality grade, as indicated below. Customers must check the quality grade of each semiconductor product before using it in a particular application.

- "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.

(Note)

(1) "NEC" as used in this statement means NEC Corporation and also includes its majority-owned subsidiaries.

(2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).